

N-Channel Enhancement-Mode Vertical DMOS FET

Features

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low C_{ISS} and fast switching speeds
- Excellent thermal stability
- Integral source-drain diode
- High input impedance and high gain

Applications

- Logic level interfaces ideal for TTL and CMOS
- Solid state relays
- Battery operated systems
- Photo-voltaic drives
- Analog switches
- General purpose line drivers
- ▶ Telecom switches

General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Part Number	Package Option	Packing		
TN2130K1-G	TO-236AB (SOT-23)	3000/Reel		

⁻G denotes a lead (Pb)-free / RoHS compliant package.

Contact factory for Wafer / Die availablity.

Devices in Wafer / Die form are lead (Pb)-free / RoHS compliant.

Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV _{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Typical Thermal Resistance

Package	$oldsymbol{ heta}_{j_{oldsymbol{a}}}$
TO-236AB (SOT-23)	203°C/W

Product Summary

BV _{DSS} /BV _{DGS}	R _{DS(ON)} (max)	V _{GS(th)} (max)
300V	25Ω	2.4V

Pin Configuration



TO-236AB (SOT-23)

Product Marking

N1TW W = Code for Week Sealed = "Green" Packaging

Package may or may not include the following marks: Si or 🌎

TO-236AB (SOT-23)

Thermal Characteristics

Package	l _D (continuous) [†]	I _D (pulsed)	Power Dissipation @T _c = 25°C	l _{DR} †	DRM
TO-236AB (SOT-23)	85mA	200mA	0.36W	85mA	200mA

Notes:

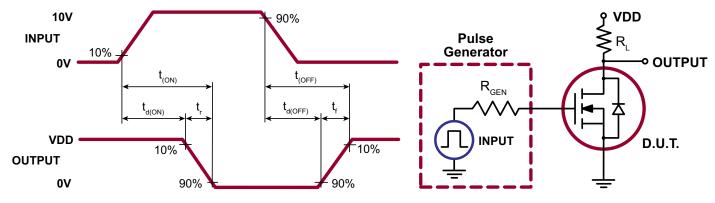
Electrical Characteristics (T_A = 25°C unless otherwise specified)

Sym	Parameter	Min	Тур	Max	Units	Conditions		
BV _{DSS}	Drain-to-source breakdown voltage	300	-	-	V	$V_{GS} = 0V, I_D = 1.0mA$		
$V_{\rm GS(th)}$	Gate threshold voltage	0.8	ı	2.4	V	$V_{GS} = V_{DS}$, $I_D = 1.0 \text{mA}$		
$\Delta V_{GS(th)}$	Change in V _{GS(th)} with temperature	-	ı	-5.5	mV/°C	$V_{GS} = V_{DS}$, $I_D = 1.0 \text{mA}$		
I _{GSS}	Gate body leakage	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
		-	-	10		$V_{GS} = 0V, V_{DS} = Max Rating$		
I _{DSS}	Zero gate voltage drain current	-	-	100	μA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0$ V, $T_A = 125$ °C		
I _{D(ON)}	On-state drain current	250	-	-	mA	$V_{GS} = 10V, V_{DS} = 25V$		
R _{DS(ON)}	Static drain-to-source on-state resistance	-	-	25	Ω	$V_{GS} = 4.5V, I_{D} = 120mA$		
$\Delta R_{DS(ON)}$	Change in R _{DS(ON)} with temperature	-	-	1.1	%/°C	$V_{GS} = 4.5V, I_{D} = 120mA$		
G _{FS}	Forward transductance	-	250	-	mmho	V _{DS} = 25V, I _D = 100mA		
C _{ISS}	Input capacitance	-	-	50		V _{GS} = 0V, V _{DS} = 25V,		
C _{oss}	Common source output capacitance	-	-	15	pF			
C _{RSS}	Reverse transfer capacitance	-	-	5.0		f = 1.0MHz		
t _{d(ON)}	Turn-on delay time	-	-	10				
t _r	Rise time	-	-	7.0		V _{DD} = 25V,		
t _{d(OFF)}	Turn-off delay time	-	-	12	ns	$I_D = 120 \text{mA},$ $R_{GEN} = 25 \Omega$		
t _f	Fall time	-	-	15		OLIV		
V _{SD}	Diode forward voltage drop	-	-	1.8	V	V _{GS} = 0V, I _{SD} = 120mA		
t _{rr}	Reverse recovery time	-	400	-	ns	V _{GS} = 0V, I _{SD} = 120mA		

Notes:

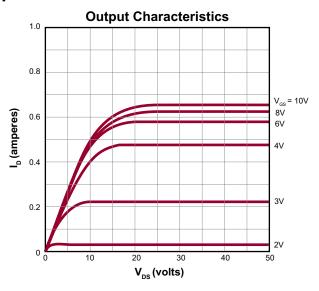
- 1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
- 2. All A.C. parameters sample tested.

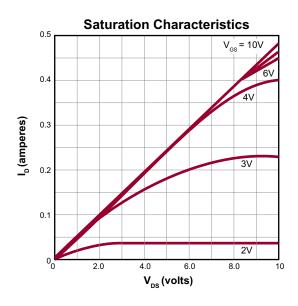
Switching Waveforms and Test Circuit

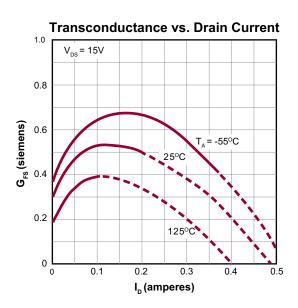


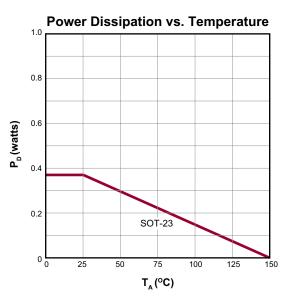
[†] I_D (continuous) is limited by max rated T_i .

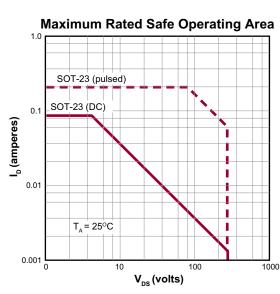
Typical Performance Curves

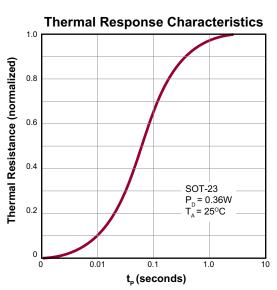




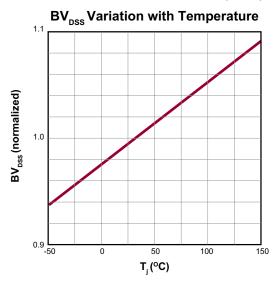


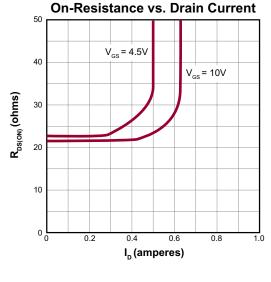


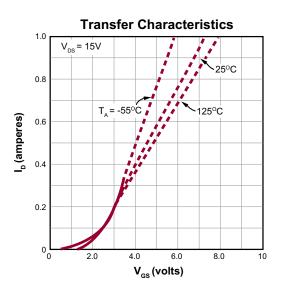


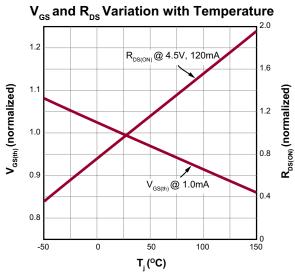


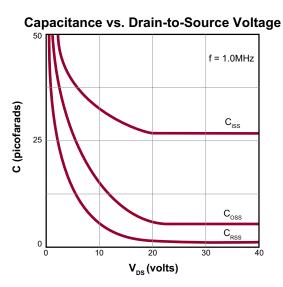
Typical Performance Curves (cont.)

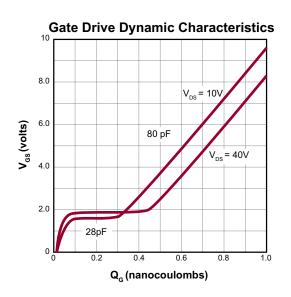






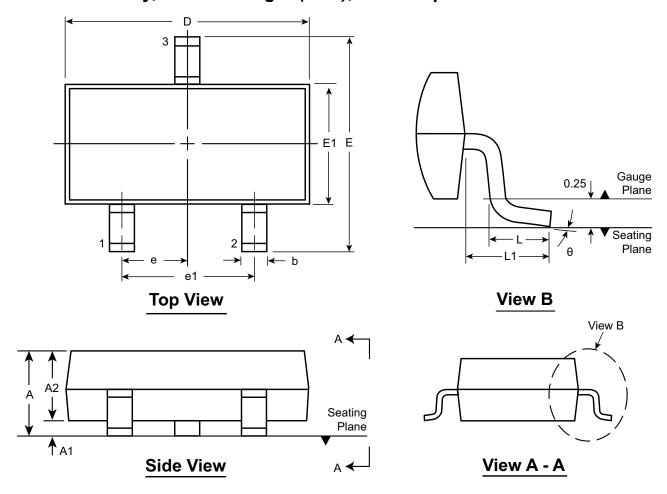






3-Lead TO-236AB (SOT-23) Package Outline (K1)

2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



Symb	ol	Α	A1	A2	b	D	E	E1	е	e1	L	L1	θ	
Dimension (mm)	MIN	0.89	0.01	0.88	0.30	2.80	2.10	1.20	0.05	1.90 BSC	4.00	0.20 [†]	0.54	0 °
	NOM	-	-	0.95	-	2.90	-	1.30	0.95 BSC		0.50	0.54 REF	-	
	MAX	1.12	0.10	1.02	0.50	3.04	2.64	1.40	ВОС	DOC	0.60	IXLI	8 º	

JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO236ABK1, Version C041309.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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[†] This dimension differs from the JEDEC drawing.